

December 12, 2003



Commissioner for Patents
 P.O. Box 1450
 Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572
 28 Davis Avenue
 Poughkeepsie, N.Y. 12603

Subject: | Serial No. 10/664,262 09/17/03 |

Yong Meng Lee et al.

METHOD OF FORMING DOUBLE-GATED
 SILICON-ON-INSULATOR (SOI)
 TRANSISTORS WITH REDUCED GATE TO
 SOURCE-DRAIN OVERLAP CAPACITANCE

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
 In An Application.

The following Patents and/or Publications are submitted to
 comply with the duty of disclosure under CFR 1.97-1.99 and
 37 CFR 1.56.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being
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 mail in an envelope addressed to: Commissioner for Patents,
 P.O. Box 1450, Alexandria, VA 22313-1450, on December 19, 2003.

Stephen B. Ackerman, Reg.# 37761

Signature/Date

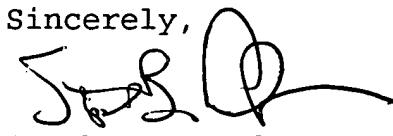
U.S. Patent 6,451,656 to Yu et al., "CMOS Inverter Configured From Double GATE MOSFET and Method of Fabricating Same," describes a double-gate transistor on semiconductor-on-insulator (SOI).

U.S. Patent 6,413,802 to Hu et al., "FinFET Transistor Structures Having a Double Gate Channel Extending Vertically From a Substrate and Methods of Manufacture," describes a double-gate FinFET on semiconductor-on-insulator (SOI).

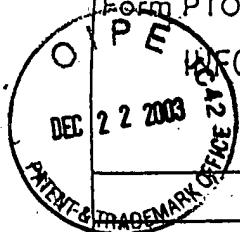
U.S. Patent 6,365,465 to Chan et al., "Self-Aligned Double-Gate MOSFET by Selective Epitaxy and Silicon Wafer Bonding Techniques," describes a process for a double-gate MOSFET on semiconductor-on-insulator (SOI).

U.S. Patent 6,396,108 to Krivokapic et al., "Self-Aligned Double Gate Silicon-On-Insulator (SOI) Device," describes a process for a double-gate MOSFET on semiconductor-on-insulator (SOI).

Sincerely,



Stephen B. Ackerman,
Reg. No. 37761



Form PTO-1449

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INFORMATION DISCLOSURE CITATION
IN AN APPLICATION
(Use several sheets if necessary)

FC 22 2013

Doctor Number (Optional)

Appetizing Names

CS-01-211

10/664, 262

Applicant Yang Meng Lee et al.

Filing Date

09/17/03

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U. S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Portion of Pages, Etc.)

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.